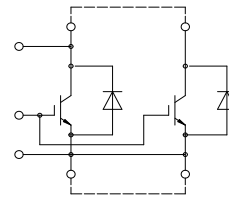
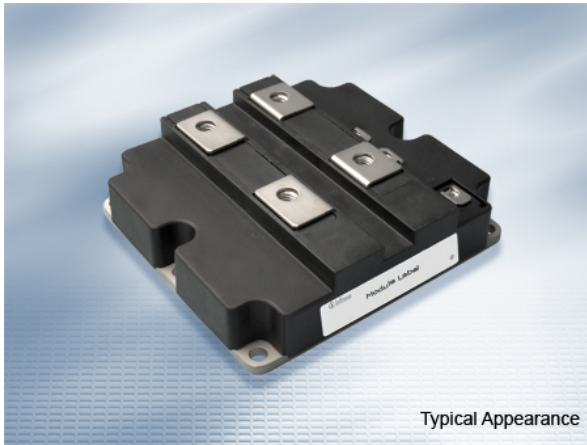


IHM-B 模块 采用软特性的沟槽栅IGBT4
 IHM-B module with soft-switching Trench-IGBT4

初步数据 / Preliminary Data



external connection
(to be done)

$V_{CES} = 1200V$

$I_{C\ nom} = 2400A / I_{CRM} = 4800A$

潜在应用

- 大功率变流器
- 电机传动
- 风力发电机

电气特性

- 提高工作结温 $T_{vj\ op}$

机械特性

- 4 kV 交流 1分钟 绝缘
- IHM B 封装
- 封装的 CTI > 400
- 高功率密度

Potential Applications

- High power converters
- Motor drives
- Wind turbines

Electrical Features

- Extended operating temperature $T_{vj\ op}$

Mechanical Features

- 4 kV AC 1min insulation
- IHM B housing
- Package with CTI > 400
- High power density

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 逆变器 / IGBT, Inverter
最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 95^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	I_{CDC} I_C	2400 3460	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	4800	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 2400\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,70 2,00 2,10	2,05	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 91,2\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,10	5,80	6,50 V
栅极电荷 Gate charge	$V_{GE} = -15 / 15\text{ V}$		Q_G	18,5		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,81		Ω
输入电容 Input capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	150		nF
反向传输电容 Reverse transfer capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	8,30		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 2400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,50 0,54 0,55		μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 2400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,33 0,33 0,33		μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 2400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 0,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	1,05 1,15 1,20		μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 2400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 0,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,20 0,23 0,24		μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 2400\text{ A}, V_{CE} = 600\text{ V}, L_{\sigma} = 54\text{ nH}$ $di/dt = 6250\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	365 460 505		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 2400\text{ A}, V_{CE} = 600\text{ V}, L_{\sigma} = 54\text{ nH}$ $du/dt = 2400\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 0,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	450 560 595		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	9600		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		12,0	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	9,75		K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

二极管, 逆变器 / Diode, Inverter 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	2400	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1 \text{ ms}$	I_{FRM}	4800	A
I^2t -值 I^2t - value	$V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	615 595	kA^2s kA^2s

特征值 / Characteristic Values

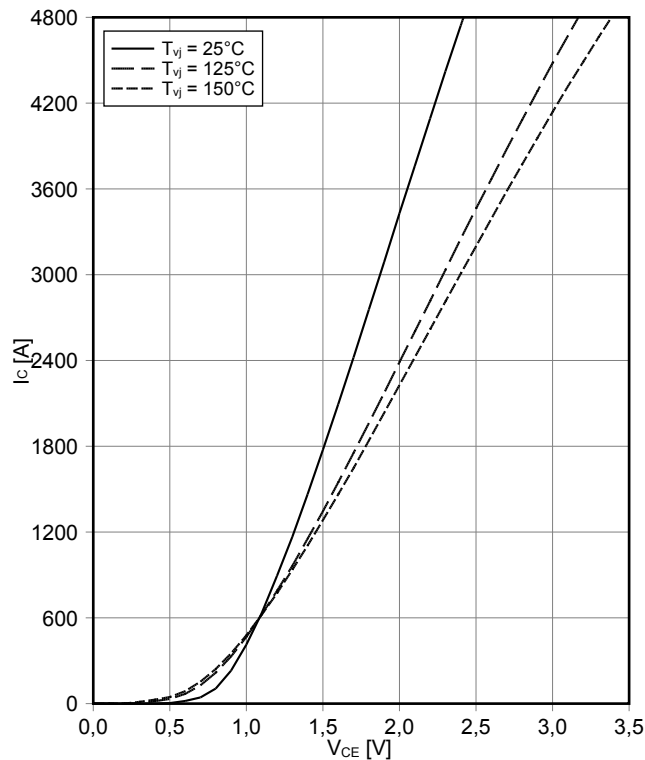
		min. typ. max.			
正向电压 Forward voltage	$I_F = 2400 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 2400 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 2400 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,80 1,75 1,70	2,35 V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 2400 \text{ A}, -di_F/dt = 6250 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	805 1150 1200	A A A
恢复电荷 Recovered charge	$I_F = 2400 \text{ A}, -di_F/dt = 6250 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	245 430 490	μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 2400 \text{ A}, -di_F/dt = 6250 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	105 185 210	mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		20,0 K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	11,0	K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj op}$	-40	150 $^{\circ}\text{C}$

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, $f = 50 \text{ Hz}, t = 1 \text{ min.}$	V_{ISOL}	4,0	kV
模块基板材料 Material of module baseplate			Cu	
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al_2O_3	
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		32,0 32,0	mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		19,0 19,0	mm
相对电痕指数 Comperative tracking index		CTI	> 400	
		min. typ. max.		
杂散电感, 模块 Stray inductance module		L_{sCE}	9,0	nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	$T_C = 25^{\circ}\text{C},$ 每个开关 / per switch	R_{CC+EE}	0,13	m Ω
储存温度 Storage temperature		T_{stg}	-40	150 $^{\circ}\text{C}$
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	4,25	5,75 Nm
端子联接扭矩 Terminal connection torque	螺丝 M4 根据相应的应用手册进行安装 Screw M4 - Mounting according to valid application note 螺丝 M8 根据相应的应用手册进行安装 Screw M8 - Mounting according to valid application note	M	1,7 8,0	- 10 Nm
重量 Weight		G	1300	g

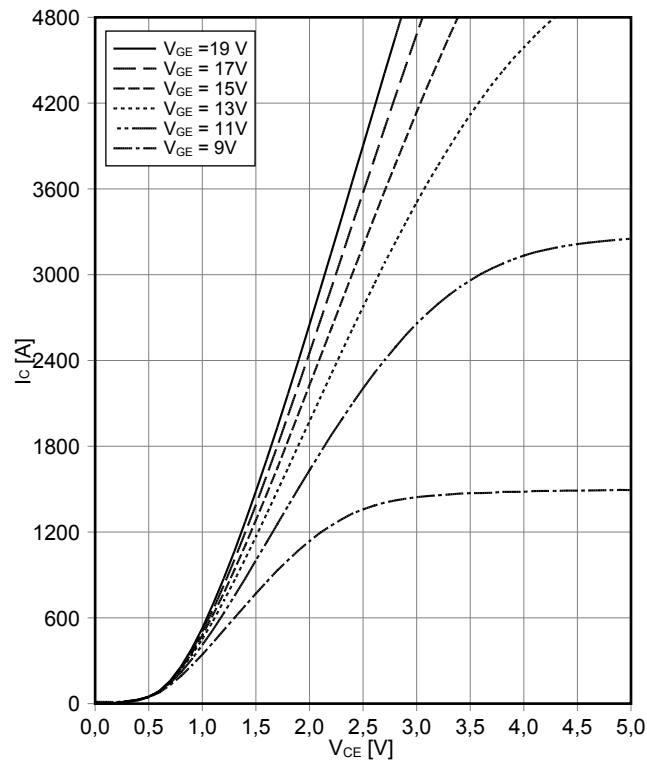
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



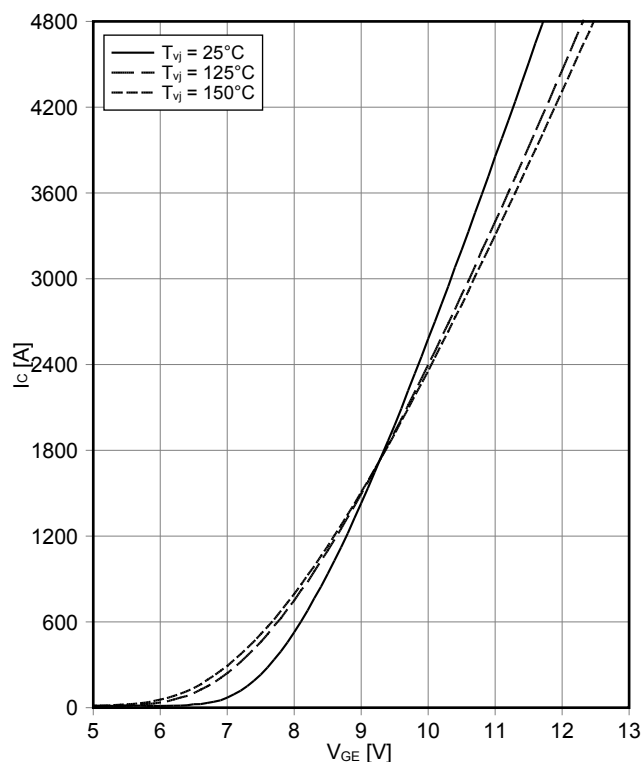
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



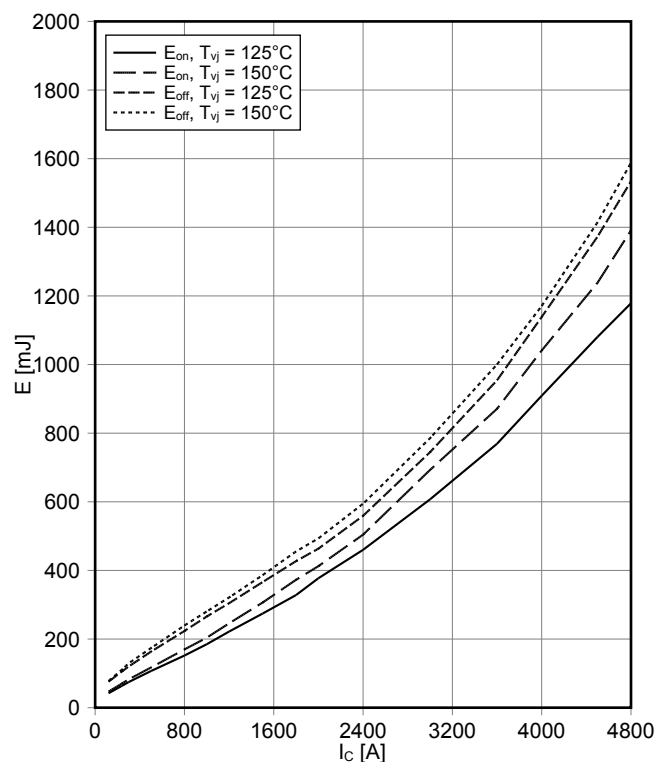
传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

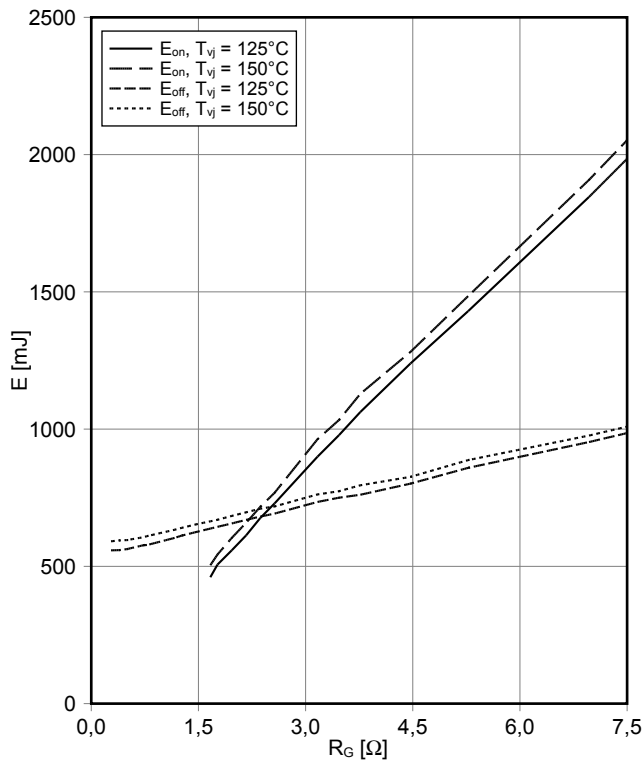
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1.6\ \Omega$, $R_{Goff} = 0.3\ \Omega$, $V_{CE} = 600\text{ V}$



初步数据 Preliminary Data

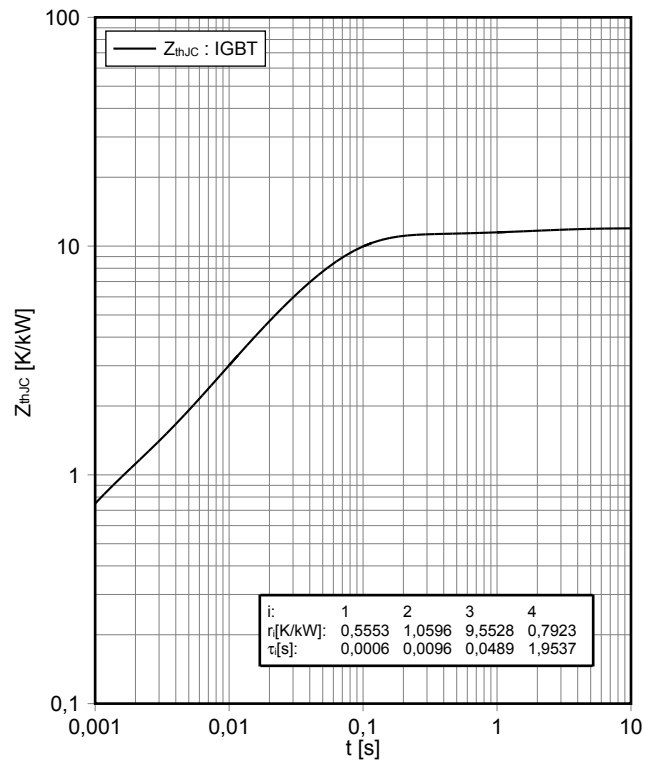
开关损耗 IGBT, 逆变器 (典型) switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}, I_C = 2400 \text{ A}, V_{CE} = 600 \text{ V}$



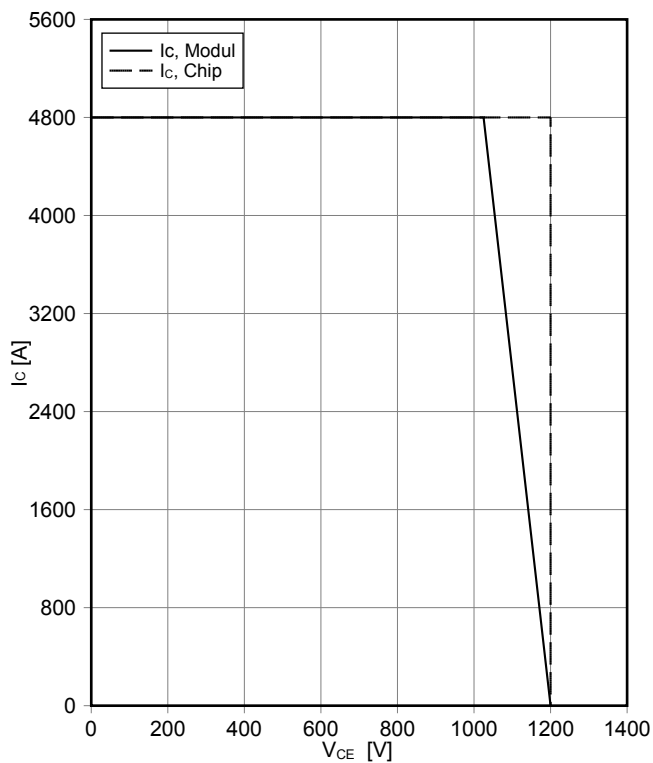
瞬态热阻抗 IGBT, 逆变器 transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$



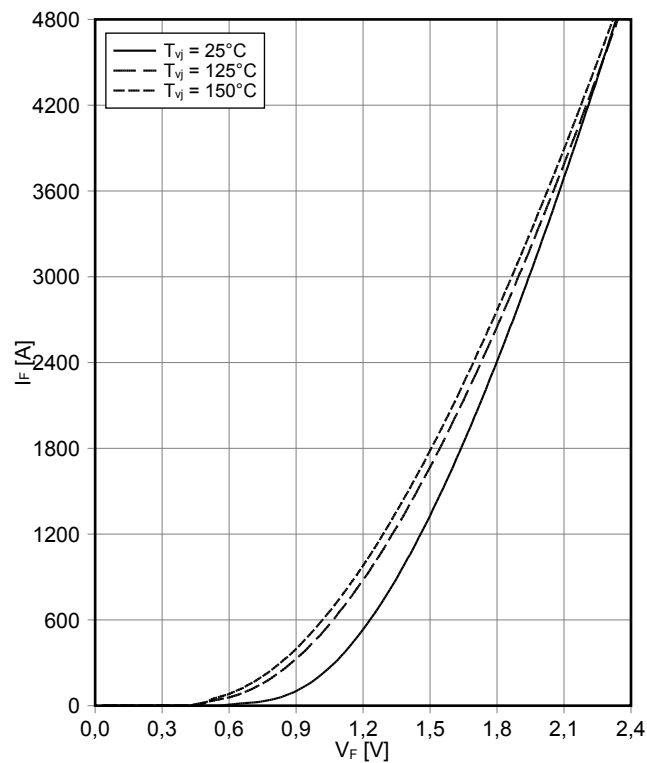
反偏安全工作区 IGBT, 逆变器 (RBSOA) reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}, R_{Goff} = 0.3 \Omega, T_{vj} = 150^\circ\text{C}$



正向偏压特性 二极管, 逆变器 (典型) forward characteristic of Diode, Inverter (typical)

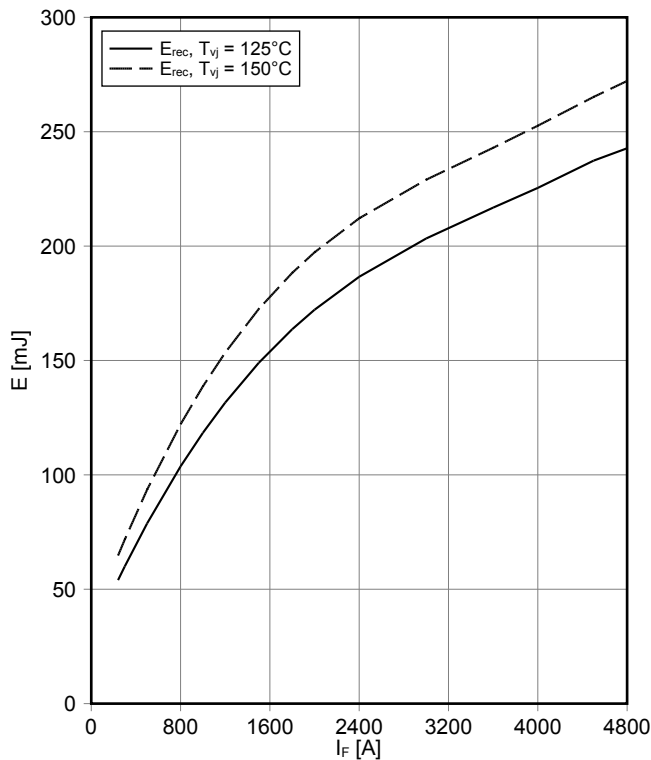
$I_F = f(V_F)$



初步数据 Preliminary Data

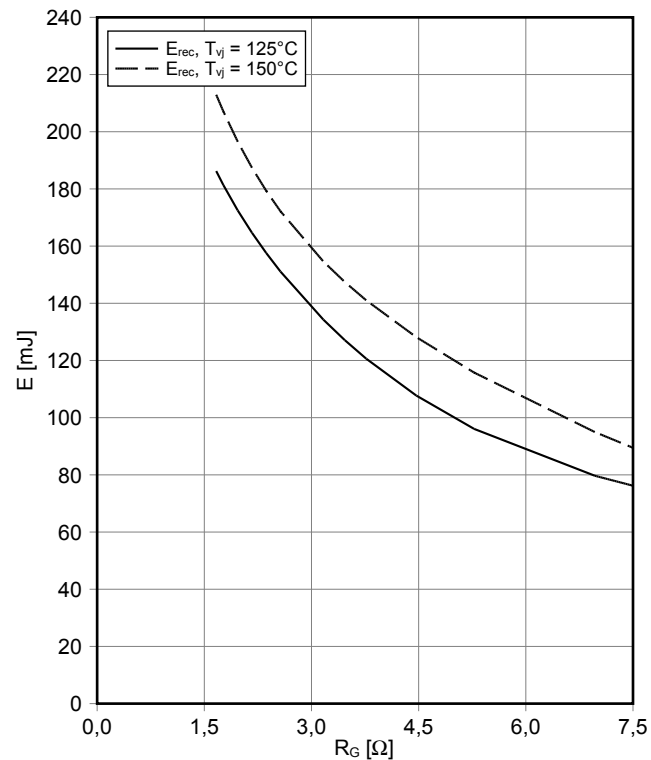
开关损耗 二极管,逆变器 (典型) switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 1.6 \Omega, V_{CE} = 600 V$



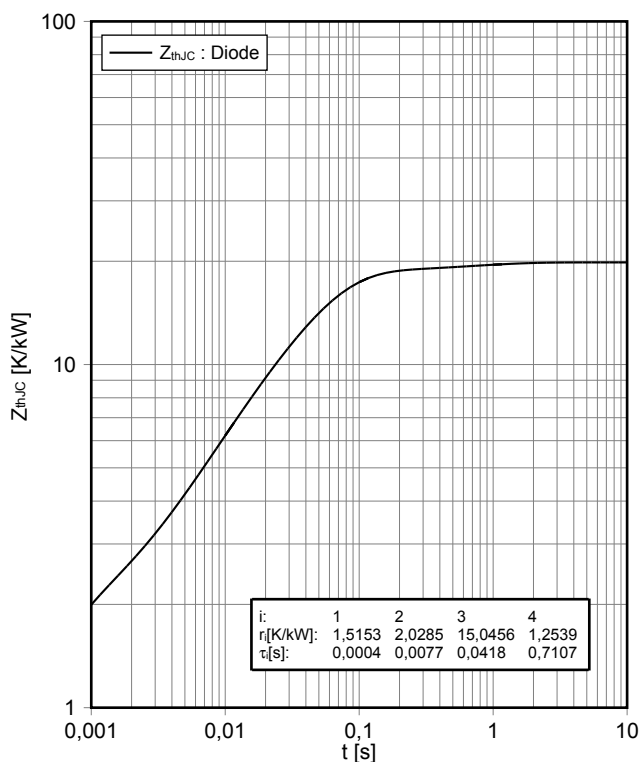
开关损耗 二极管,逆变器 (典型) switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 2400 A, V_{CE} = 600 V$

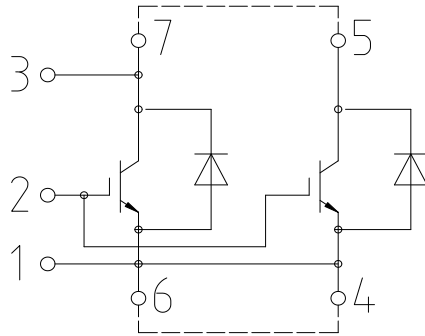


瞬态热阻抗 二极管,逆变器 transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$

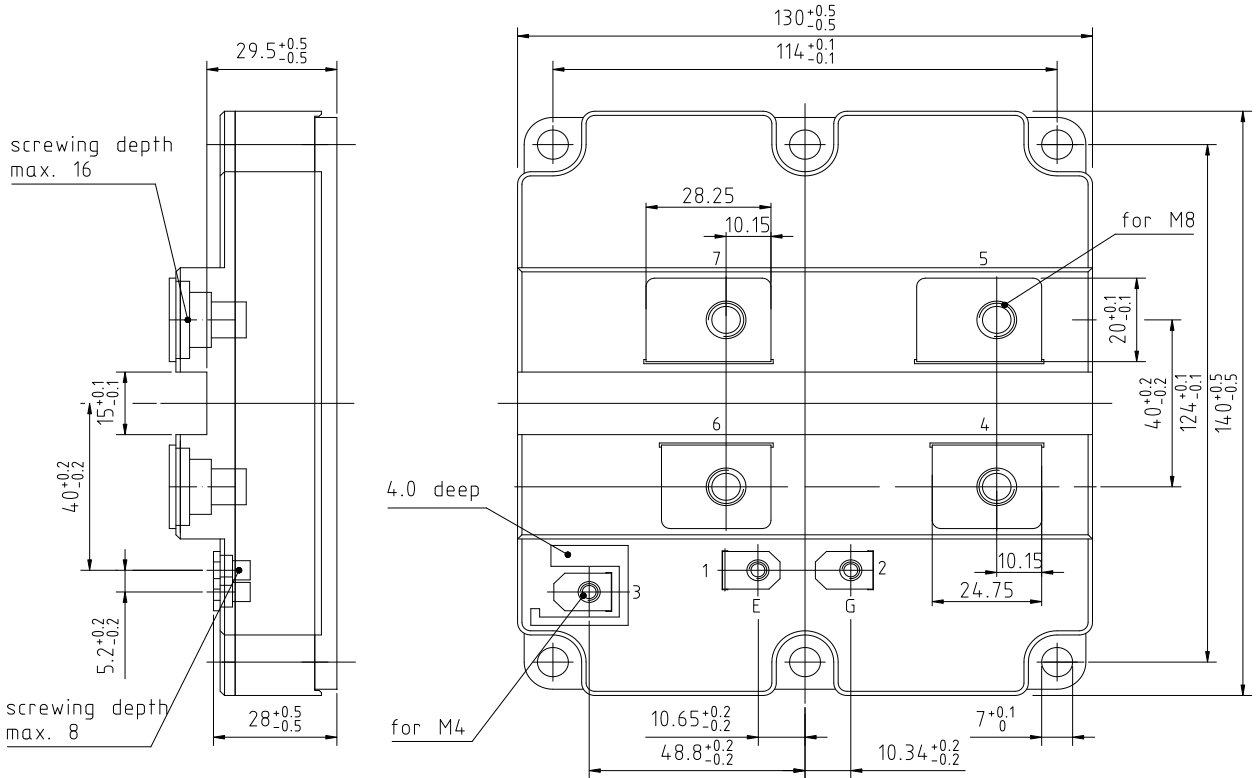
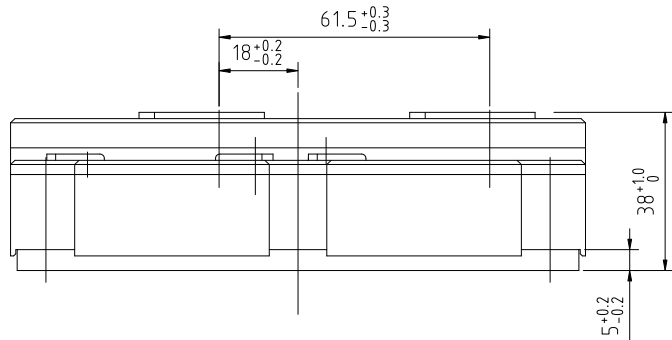


接线图 / Circuit diagram



external connection
(to be done)

封装尺寸 / Package outlines



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